

Silicon PNP Power Transistors

2SA1187

DESCRIPTION

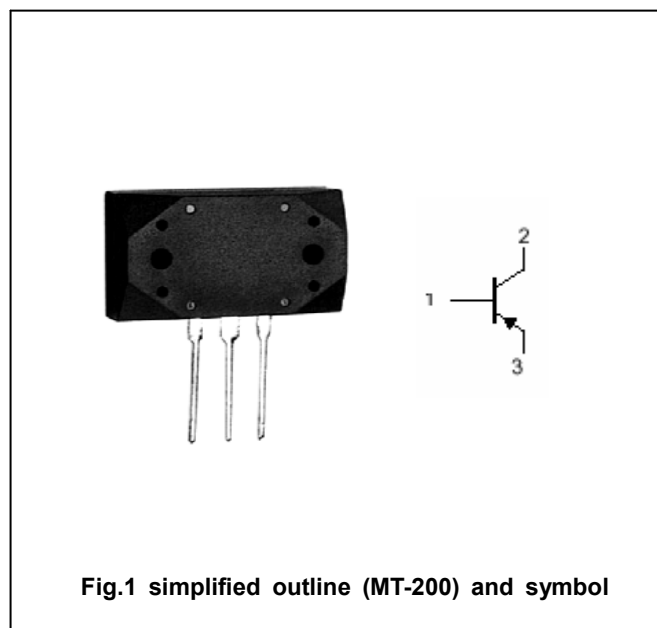
- With MT-200 package
- High current capability

APPLICATIONS

- Audio and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
I_B	Base current		-2	A
P_C	Collector power dissipation	$T_C = 25 \square$	120	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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2SA1187**CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25mA$; $I_B=0$	-150			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A$; $I_B=-0.5A$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-150V$; $I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-0.1	mA
h_{FE}	DC current gain	$I_C=-3A$; $V_{CE}=-4V$	50			
C_{ob}	Output capacitance	$I_E=0$; $V_{CB}=-80V$; $f=1MHz$		110		pF
f_T	Transition frequency	$I_E=1A$; $V_{CE}=-12V$		60		MHz

◆ **h_{FE} Classifications**

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE

